



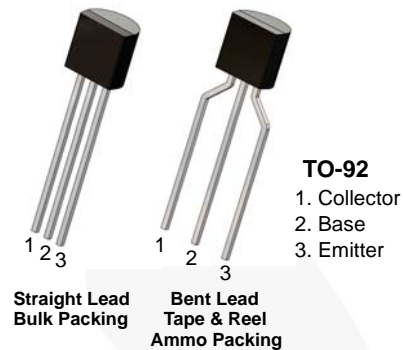
September 2015

BC337 / BC338

NPN Epitaxial Silicon Transistor

Features

- Switching and Amplifier Applications
- Suitable for AF-Driver Stages and Low-Power Output Stages
- Complement to BC327 / BC328



Ordering Information

Part Number	Top Mark	Package	Packing Method
BC33716BU	BC33716	TO-92 3L	Bulk
BC33716TA	BC33716	TO-92 3L	Ammo
BC33716TFR	BC33716	TO-92 3L	Tape and Reel
BC33725BU	BC33725	TO-92 3L	Bulk
BC33725TA	BC33725	TO-92 3L	Ammo
BC33725TAR	BC33725	TO-92 3L	Ammo
BC33725TF	BC33725	TO-92 3L	Tape and Reel
BC33725TFR	BC33725	TO-92 3L	Tape and Reel
BC33740BU	BC33740	TO-92 3L	Bulk
BC33740TA	BC33740	TO-92 3L	Ammo
BC33825TA	BC33825	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V_{CES}	Collector-Emitter Voltage	BC337	50	V
		BC338	30	
V_{CEO}	Collector-Emitter Voltage	BC337	45	V
		BC338	25	
V_{EBO}	Emitter-Base Voltage	5	V	
I_C	Collector Current (DC)	800	mA	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature	-55 to 150	$^\circ\text{C}$	

Thermal Characteristics⁽¹⁾Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	625	mW
	Derate Above 25°C	5.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C}/\text{W}$

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

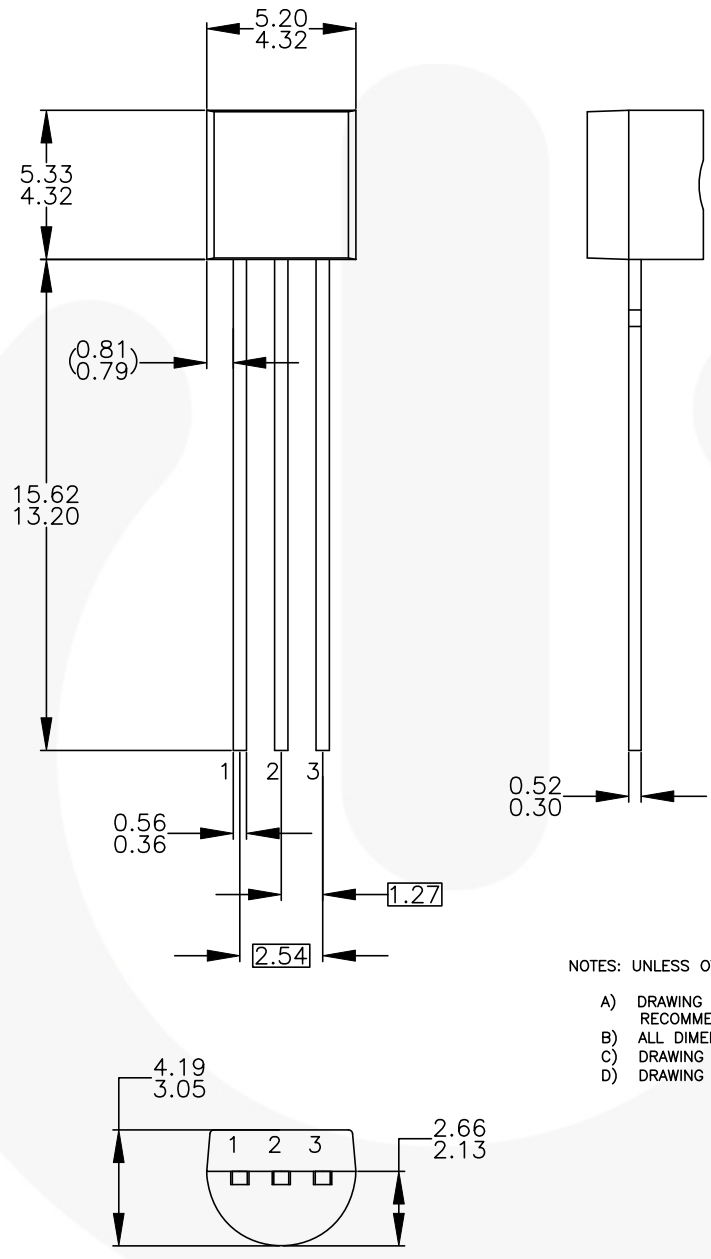
Electrical CharacteristicsValues are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
BV_{CEO}	Collector-Emitter Breakdown Voltage	BC337	$I_C = 10\text{ mA}, I_B = 0$	45			V
		BC338		25			
BV_{CES}	Collector-Emitter Breakdown Voltage	BC337	$I_C = 0.1\text{ mA}, V_{BE} = 0$	50			V
		BC338		30			
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.1\text{ mA}, I_C = 0$	5			V	
I_{CES}	Collector Cut-Off Current	BC337	$V_{CE} = 45\text{ V}, I_B = 0$		2	100	nA
		BC338	$V_{CE} = 25\text{ V}, I_B = 0$		2	100	
h_{FE1}	DC Current Gain		$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100		630	
h_{FE2}			$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$	60			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.7	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$			1.2	V	
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 50\text{ MHz}$		100		MHz	
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		12		pF	

 h_{FE} Classification

Classification	16	25	40
h_{FE1}	100 ~ 250	160 ~ 400	250 ~ 630
h_{FE2}	60 ~	100 ~	170 ~

Physical Dimensions

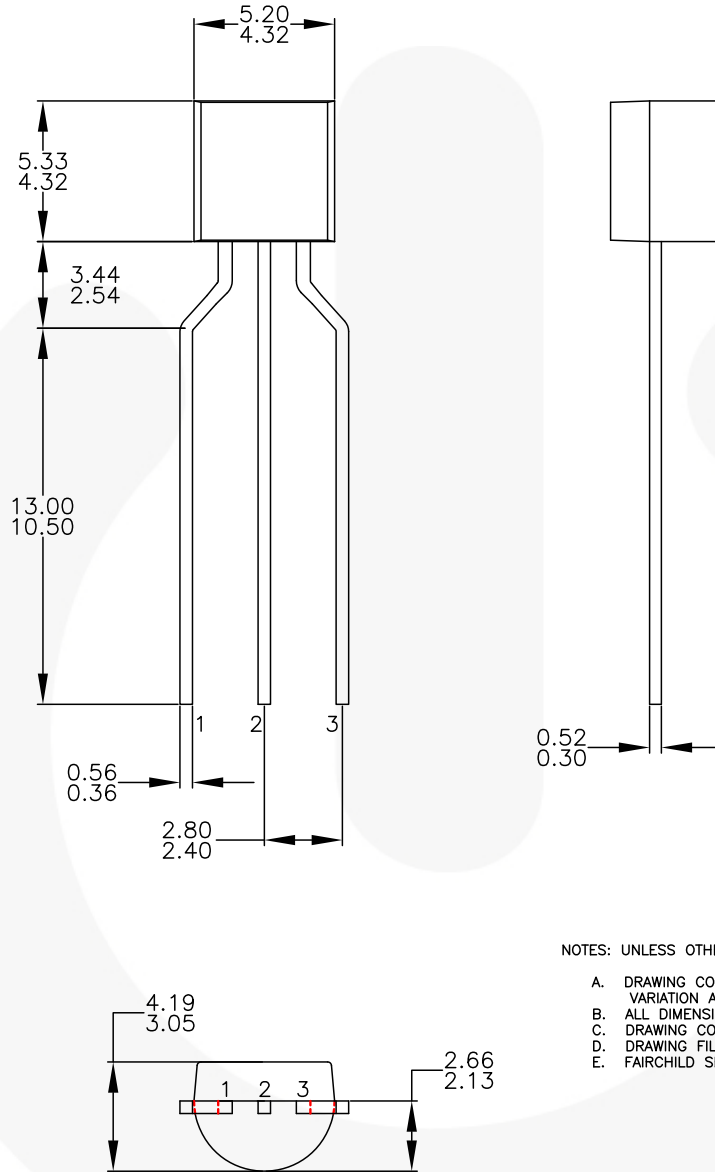


- NOTES: UNLESS OTHERWISE SPECIFIED
- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DRAWING CONFORMS TO ASME Y14.5M-2009.
 - D) DRAWING FILENAME: MKT-ZA03DREV4.



Figure 1. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREVS.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 2. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type